



REVISION HISTORY

<u>Revision</u>	<u>Description</u>	<u>Issue Date</u>
Rev. 1.0	Initial Issue	Nov.1.2007
Rev. 1.1	Added I _{SB} Spec.	Feb.1.2008
Rev. 1.2	Revised <u>ORDERING INFORMATION</u>	Feb.13.2008
Rev. 1.3	Added SL Spec.	Jul.2.2008
Rev. 1.4	Added I _{SB1} /I _{DR} values when T _A = 25°C and T _A = 40°C Revised <u>FEATURES & ORDERING INFORMATION</u> Lead free and green package available to Green package available Added packing type in <u>ORDERING INFORMATION</u> Deleted T _{SOLDER} in <u>ABSOLUTE MAXIMUM RATINGS</u>	Mar.30.2009
Rev. 1.5	Revised <u>ORDERING INFORMATION</u> in page 11	Aug.30.2010
Rev. 1.6	Deleted E grade	Apr.12.2011
Rev. 1.7	Added -45ns Spec.	Oct.1.2015
Rev. 1.8	Deleted <u>WRITE CYCLE</u> Notes : 1.WE#,CE#, LB#, UB# must be high during all address transitions.in page 8	Jun.29.2016
Rev. 1.9	Deleted -45ns Spec.	Nov.14.2016
Rev. 2.0	1. Deleted <u>FEATURES</u> Standby current : 1.5μA (TYP.) SL-version--Page 1 2. Deleted <u>PRODUCT FAMILY</u> Standby(I _{SB1} ,TYP.) : 1.5μA(SL) --Page 1 3. Deleted <u>DC ELECTRICAL CHARACTERISTICS</u> : Standby Power Supply Current : I _{SB1} --- Page4 4. Deleted <u>DC ELECTRICAL CHARACTERISTICS</u> : Notes: 5 --- Page 4 5. Deleted <u>DATA RETENTION CHARACTERISTICS</u> : Data Retention Current: I _{DR} --- Page 9 6. Revised <u>ORDERING INFORMATION</u> in Page 12~Page15	Jun.18.2024

FEATURES

- Fast access time : 55/70ns
- Low power consumption:
Operating current : 30/20mA (TYP.)
Standby current : 5 μ A (TYP.) LL-version
- Single 2.7V ~ 3.6V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data byte control : LB# (DQ0 ~ DQ7)
UB# (DQ8 ~ DQ15)
- Data retention voltage : 1.2V (MIN.)
- **Green package available**
- Package : 44-pin 400mil TSOP II
48-ball 6mm x 8mm TFBGA

GENERAL DESCRIPTION

The LY62L51216 is a 8,388,608-bit low power CMOS static random access memory organized as 524,288 words by 16 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

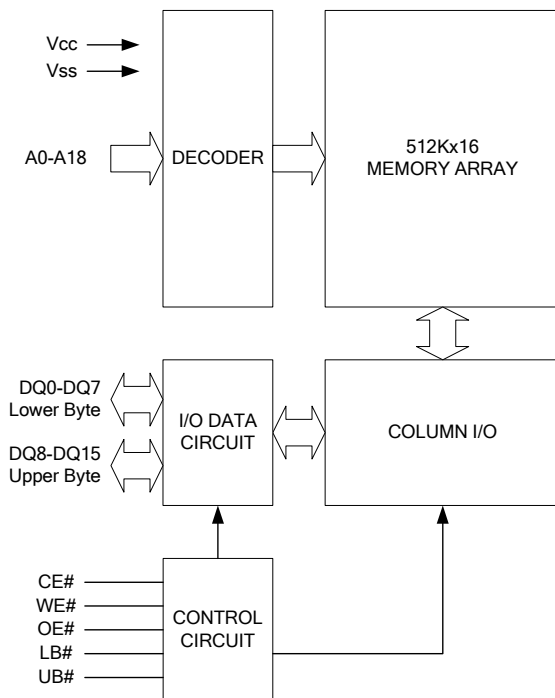
The LY62L51216 is well designed for low power application, and particularly well suited for battery back-up nonvolatile memory application.

The LY62L51216 operates from a single power supply of 2.7V ~ 3.6V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product Family	Operating Temperature	V _{CC} Range	Speed	Power Dissipation	
				Standby(I _{SB1} , TYP.)	Operating(I _{CC} , TYP.)
LY62L51216	0 ~ 70°C	2.7 ~ 3.6V	55/70ns	5 μ A(LL)	30/20mA
LY62L51216(I)	-40 ~ 85°C	2.7 ~ 3.6V	55/70ns	5 μ A(LL)	30/20mA

FUNCTIONAL BLOCK DIAGRAM

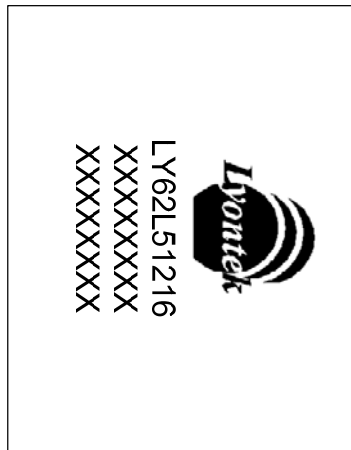
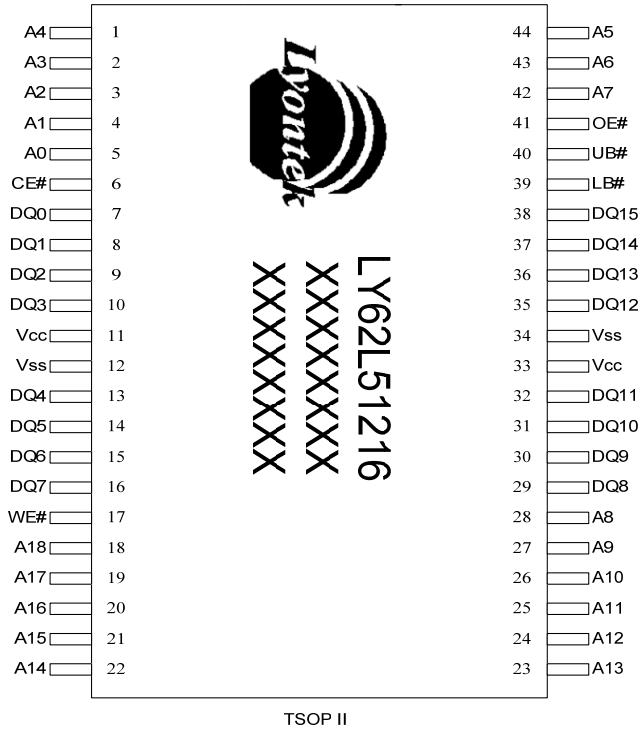


PIN DESCRIPTION

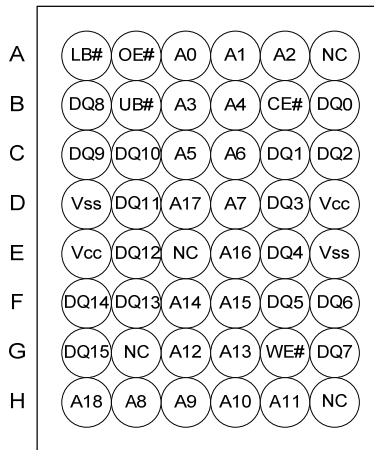
SYMBOL	DESCRIPTION
A0 - A18	Address Inputs
DQ0 - DQ15	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
LB#	Lower Byte Control
UB#	Upper Byte Control
V _{CC}	Power Supply
V _{SS}	Ground



PIN CONFIGURATION



TFPGA(Top View)



TFPGA (See through with Top View)



ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V _{CC} relative to V _{SS}	V _{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to V _{SS}	V _{T2}	-0.5 to V _{CC} +0.5	V
Operating Temperature	T _A	0 to 70(C grade)	°C
		-40 to 85(I grade)	
Storage Temperature	T _{STG}	-65 to 150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	LB#	UB#	I/O OPERATION		SUPPLY CURRENT
						DQ0-DQ7	DQ8-DQ15	
Standby	H	X	X	X	X	High – Z	High – Z	I _{SB} , I _{SB1}
	X	X	X	H	H	High – Z	High – Z	
Output Disable	L	H	H	L	X	High – Z	High – Z	I _{CC} , I _{CC1}
	L	H	H	X	L	High – Z	High – Z	
Read	L	L	H	L	H	D _{OUT}	High – Z	I _{CC} , I _{CC1}
	L	L	H	H	L	High – Z	D _{OUT}	
	L	L	H	L	L	D _{OUT}	D _{OUT}	
Write	L	X	L	L	H	D _{IN}	High – Z	I _{CC} , I _{CC1}
	L	X	L	H	L	High – Z	D _{IN}	
	L	X	L	L	L	D _{IN}	D _{IN}	

Note: H = V_{IH}, L = V_{IL}, X = Don't care.



DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP. *4	MAX.	UNIT	
Supply Voltage	V_{CC}		2.7	3.0	3.6	V	
Input High Voltage	V_{IH}^{*1}		2.2	-	$V_{CC}+0.3$	V	
Input Low Voltage	V_{IL}^{*2}		- 0.2	-	0.6	V	
Input Leakage Current	I_{LI}	$V_{CC} \geq V_{IN} \geq V_{SS}$	- 1	-	1	μA	
Output Leakage Current	I_{LO}	$V_{CC} \geq V_{OUT} \geq V_{SS}$, Output Disabled	- 1	-	1	μA	
Output High Voltage	V_{OH}	$I_{OH} = -1mA$	2.2	2.7	-	V	
Output Low Voltage	V_{OL}	$I_{OL} = 2mA$	-	-	0.4	V	
Average Operating Power supply Current	I_{CC}	Cycle time = Min. CE# = V_{IL} , $I_{I/O} = 0mA$ Other pins at V_{IL} or V_{IH}	- 55	-	30	40	mA
			- 70	-	20	30	mA
	I_{CC1}	Cycle time = $1\mu s$ CE# = 0.2V , $I_{I/O} = 0mA$ Other pins at 0.2V or $V_{CC} - 0.2V$	-	4	8	mA	
Standby Power Supply Current	I_{SB}	CE# = V_{IH} . Other pins at V_{IL} or V_{IH}	-	0.15	1	mA	
	I_{SB1}	CE# $\geq V_{CC} - 0.2V$ Others at 0.2V or $V_{CC} - 0.2V$	LL	-	5	30	μA
LLI			-	5	50	μA	

Notes:

- $V_{IH}(\max) = V_{CC} + 3.0V$ for pulse width less than 10ns.
- $V_{IL}(\min) = V_{SS} - 3.0V$ for pulse width less than 10ns.
- Over/Undershoot specifications are characterized, not 100% tested.
- Typical values are included for reference only and are not guaranteed or tested.
Typical values are measured at $V_{CC} = V_{CC}(\text{TYP.})$ and $T_A = 25^\circ C$

CAPACITANCE ($T_A = 25^\circ C$, $f = 1.0MHz$)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0.2V to $V_{CC} - 0.2V$
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30pF + 1TTL$, $I_{OH}/I_{OL} = -1mA/2mA$



AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

PARAMETER	SYM.	LY62L51216-55		LY62L51216-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t _{RC}	55	-	70	-	ns
Address Access Time	t _{AA}	-	55	-	70	ns
Chip Enable Access Time	t _{ACE}	-	55	-	70	ns
Output Enable Access Time	t _{OE}	-	30	-	35	ns
Chip Enable to Output in Low-Z	t _{CLZ} *	10	-	10	-	ns
Output Enable to Output in Low-Z	t _{OLZ} *	5	-	5	-	ns
Chip Disable to Output in High-Z	t _{CHZ} *	-	20	-	25	ns
Output Disable to Output in High-Z	t _{OHZ} *	-	20	-	25	ns
Output Hold from Address Change	t _{OH}	10	-	10	-	ns
LB#, UB# Access Time	t _{BA}	-	55	-	70	ns
LB#, UB# to High-Z Output	t _{BHZ} *	-	25	-	30	ns
LB#, UB# to Low-Z Output	t _{BLZ} *	10	-	10	-	ns

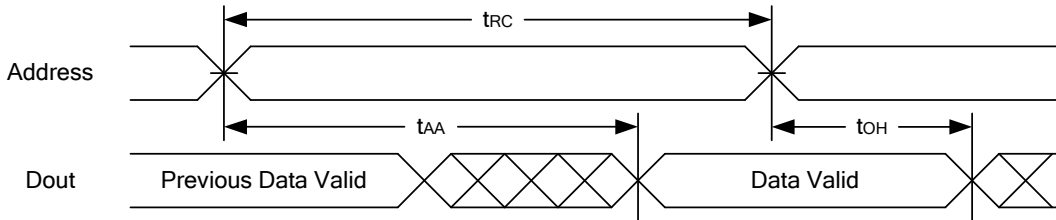
(2) WRITE CYCLE

PARAMETER	SYM.	LY62L51216-55		LY62L51216-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t _{WC}	55	-	70	-	ns
Address Valid to End of Write	t _{AW}	50	-	60	-	ns
Chip Enable to End of Write	t _{CW}	50	-	60	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	ns
Write Pulse Width	t _{WP}	45	-	55	-	ns
Write Recovery Time	t _{WR}	0	-	0	-	ns
Data to Write Time Overlap	t _{DW}	25	-	30	-	ns
Data Hold from End of Write Time	t _{DH}	0	-	0	-	ns
Output Active from End of Write	t _{OW} *	5	-	5	-	ns
Write to Output in High-Z	t _{WHZ} *	-	20	-	25	ns
LB#, UB# Valid to End of Write	t _{BW}	45	-	60	-	ns

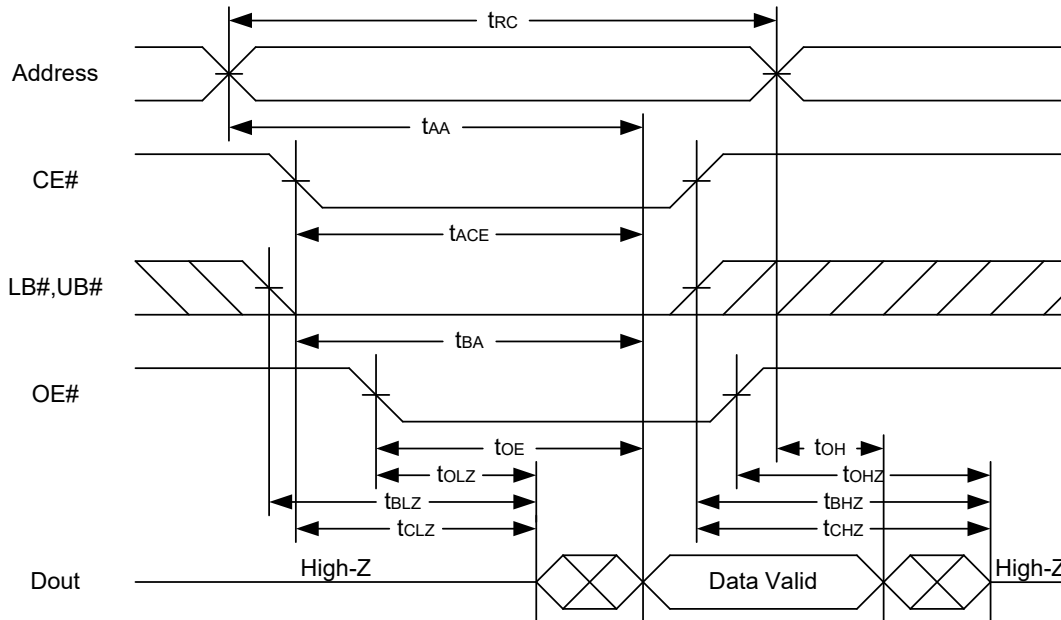
*These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)

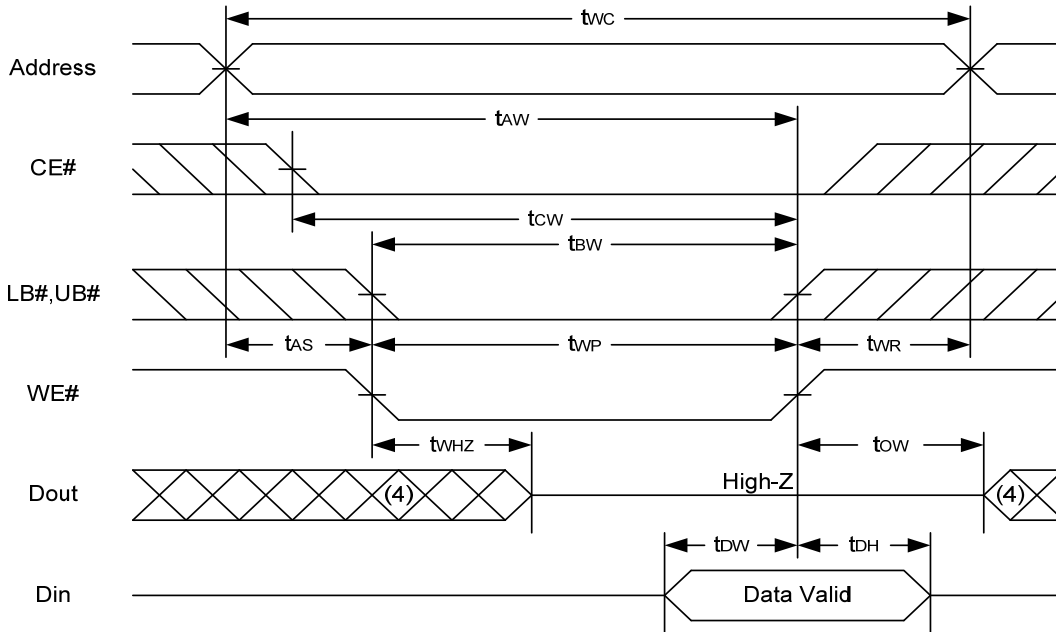


Notes :

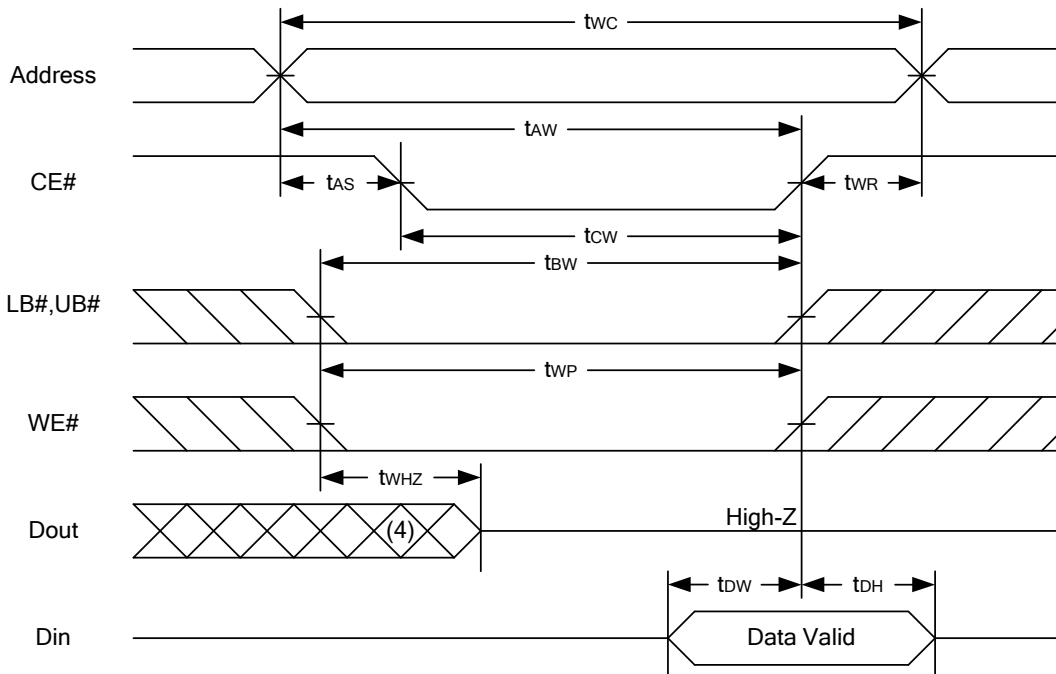
1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low, LB# or UB# = low.
3. Address must be valid prior to or coincident with CE# = low, LB# or UB# = low transition; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{BLZ} , t_{OLZ} , t_{CHZ} , t_{BHZ} and t_{OHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{BHZ} is less than t_{BLZ} , t_{OHZ} is less than t_{OLZ} .



WRITE CYCLE 1 (WE# Controlled) (1,2,4,5)

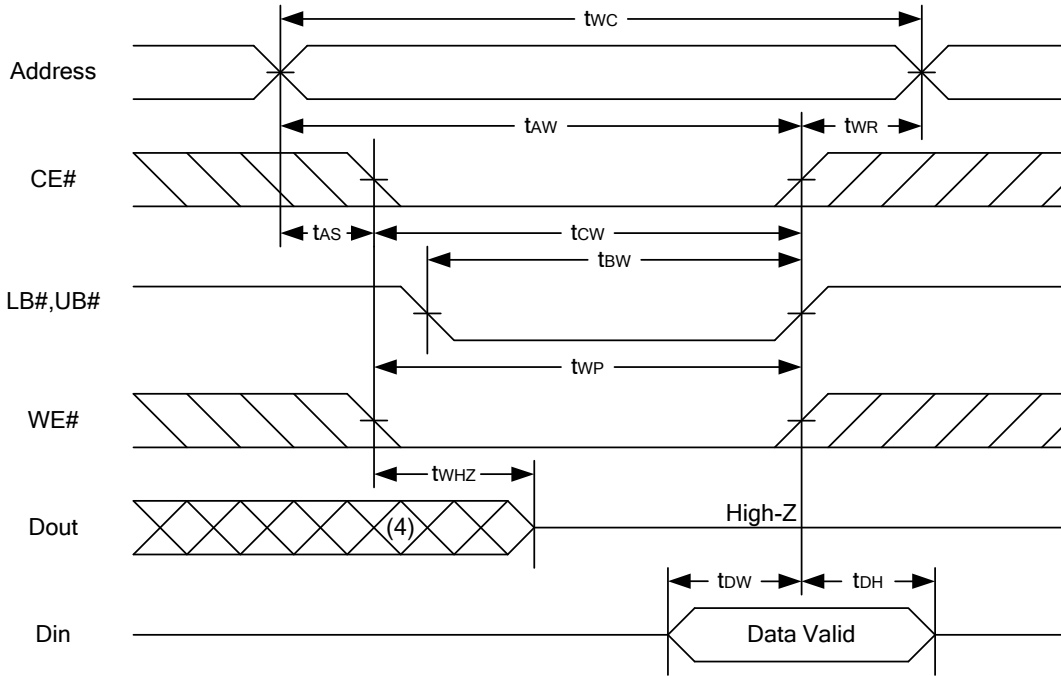


WRITE CYCLE 2 (CE# Controlled) (1,4,5)





WRITE CYCLE 3 (LB#,UB# Controlled) (1,4,5)



Notes :

1. A write occurs during the overlap of a low CE#, low WE#, LB# or UB# = low.
2. During a WE# controlled write cycle with OE# low, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
3. During this period, I/O pins are in the output state, and input signals must not be applied.
4. If the CE#, LB#, UB# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
5. t_{OW} and t_{WHZ} are specified with $C_L = 5\text{pF}$. Transition is measured $\pm 500\text{mV}$ from steady state.



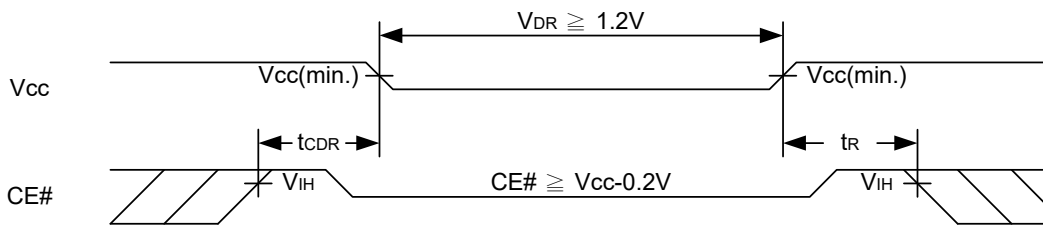
DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V _{DR}	CE# ≥ V _{CC} - 0.2V	1.2	-	3.6	V
Data Retention Current	I _{DR}	V _{CC} = 1.2V CE# ≥ V _{CC} - 0.2V Other pins at 0.2V or V _{CC} -0.2V	LL	2	25	μA
			LLI	2	40	μA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC} *	-	-	ns

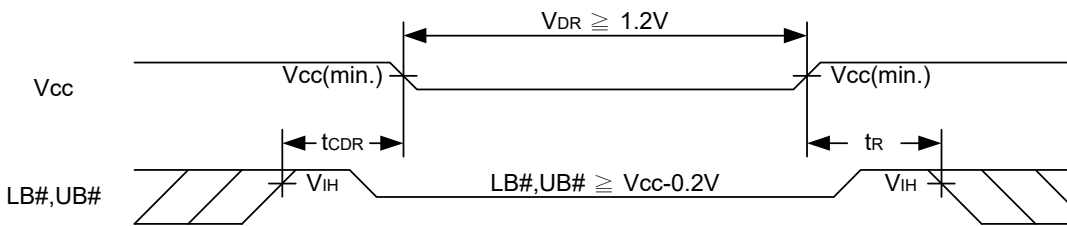
t_{RC}* = Read Cycle Time

DATA RETENTION WAVEFORM

Low V_{CC} Data Retention Waveform (1) (CE# controlled)



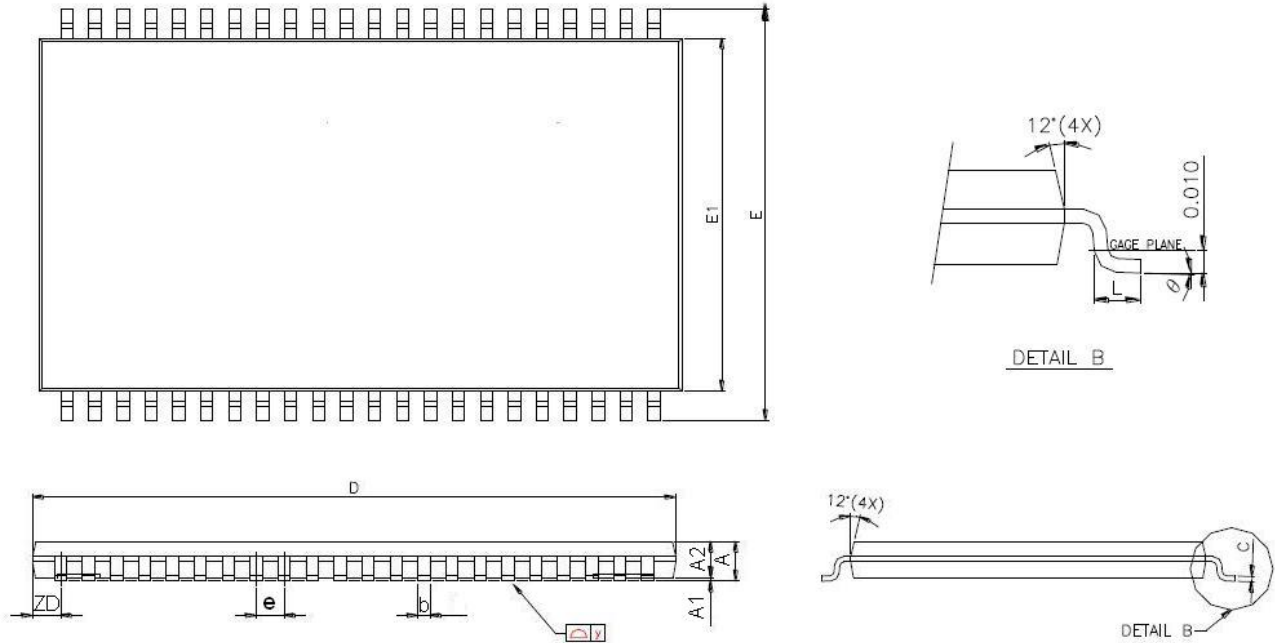
Low V_{CC} Data Retention Waveform (2) (LB#, UB# controlled)





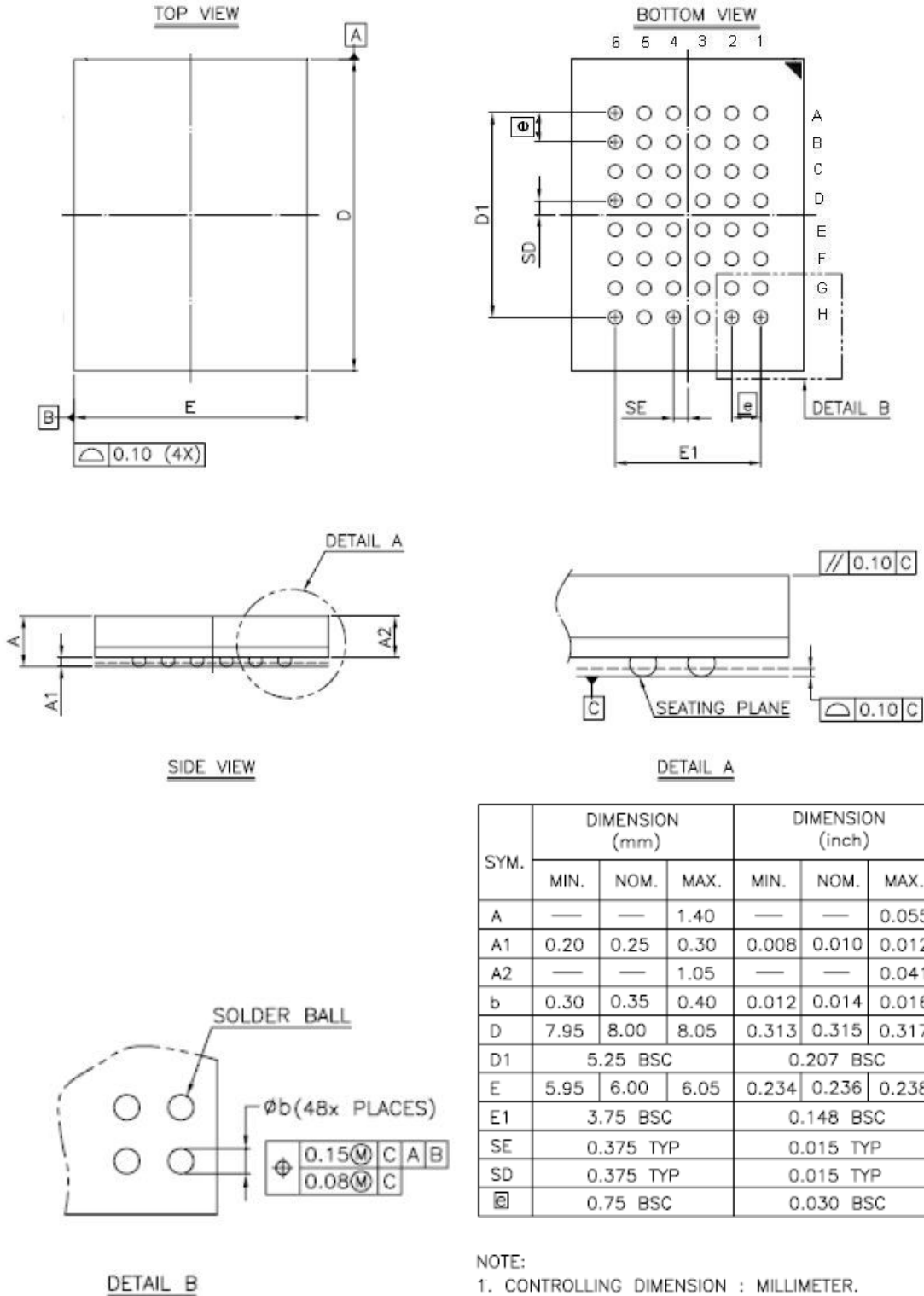
PACKAGE OUTLINE DIMENSION

44-pin 400mil TSOP II Package Outline Dimension



SYMBOLS	DIMENSIONS IN MILLMETERS			DIMENSIONS IN MILS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	-	-	1.20	-	-	47.2
A1	0.05	0.10	0.15	2.0	3.9	5.9
A2	0.95	1.00	1.05	37.4	39.4	41.3
b	0.30	-	0.45	11.8	-	17.7
c	0.12	-	0.21	4.7	-	8.3
D	18.212	18.415	18.618	717	725	733
E	11.506	11.760	12.014	453	463	473
E1	9.957	10.160	10.363	392	400	408
e	-	0.800	-	-	31.5	-
L	0.40	0.50	0.60	15.7	19.7	23.6
ZD	-	0.805	-	-	31.7	-
y	-	-	0.076	-	-	3
θ	0°	3°	6°	0°	3°	6°

48-ball 6mm × 8mm TFBGA Package Outline Dimension





ORDERING INFORMATION

[Production Status: M/P]

Package Type	Access Time (Speed/ns)	Power Type	Temperature Range(°C)	Packing Type	Lyontek Item No.
44-pin (400mil) TSOP II	55	Ultra Low Power	0°C~70°C	Tray	LY62L51216ML-55LL
				Tape Reel	LY62L51216ML-55LLT
			-40°C~85°C	Tray	LY62L51216ML-55LLI
				Tape Reel	LY62L51216ML-55LLIT
	70	Ultra Low Power	0°C~70°C	Tray	LY62L51216ML-70LL
				Tape Reel	LY62L51216ML-70LLT
			-40°C~85°C	Tray	LY62L51216ML-70LLI
				Tape Reel	LY62L51216ML-70LLIT



ORDERING INFORMATION

[Production Status: M/P]

Package Type	Access Time (Speed/ns)	Power Type	Temperature Range(°C)	Packing Type	Lyontek Item No.
48-ball (6mm x 8mm) TFBGA	55	Ultra Low Power	0°C~70°C	Tray	LY62L51216GL-55LL
				Tape Reel	LY62L51216GL-55LLT
			-40°C~85°C	Tray	LY62L51216GL-55LLI
				Tape Reel	LY62L51216GL-55LLIT
	70	Ultra Low Power	0°C~70°C	Tray	LY62L51216GL-70LL
				Tape Reel	LY62L51216GL-70LLT
			-40°C~85°C	Tray	LY62L51216GL-70LLI
				Tape Reel	LY62L51216GL-70LLIT



ORDERING INFORMATION

[Production Status: **EOL**]

Power Type : Special Ultra Low Power

Package Type	Access Time (Speed/ns)	Temperature Range(°C)	Packing Type	EOL Item No.	Substitute Product
44-pin (400mil) TSOP II	55	0°C~70°C	Tray	LY62L51216ML-55SL	LY62L51216BML-45SL
			Tape Reel	LY62L51216ML-55SLT	LY62L51216BML-45SLT
		-40°C~85°C	Tray	LY62L51216ML-55SLI	LY62L51216BML-45SLI
			Tape Reel	LY62L51216ML-55SLIT	LY62L51216BML-45SLIT
	70	0°C~70°C	Tray	LY62L51216ML-70SL	LY62L51216BML-45SL
			Tape Reel	LY62L51216ML-70SLT	LY62L51216BML-45SLT
		-40°C~85°C	Tray	LY62L51216ML-70SLI	LY62L51216BML-45SLI
			Tape Reel	LY62L51216ML-70SLIT	LY62L51216BML-45SLIT



ORDERING INFORMATION

[Production Status: **EOL**]

Power Type : Special Ultra Low Power

Package Type	Access Time (Speed/ns)	Temperature Range(°C)	Packing Type	Lyontek Item No.	
48-ball (6mm x 8mm) TFBGA	55	0°C~70°C	Tray	LY62L51216GL-55SL	LY62L51216GL-55LL
			Tape Reel	LY62L51216GL-55SLT	LY62L51216GL-55LLT
		-40°C~85°C	Tray	LY62L51216GL-55SLI	LY62L51216GL-55LLI
			Tape Reel	LY62L51216GL-55SLIT	LY62L51216GL-55LLIT
	70	0°C~70°C	Tray	LY62L51216GL-70SL	LY62L51216GL-70LL
			Tape Reel	LY62L51216GL-70SLT	LY62L51216GL-70LLT
		-40°C~85°C	Tray	LY62L51216GL-70SLI	LY62L51216GL-70LLI
			Tape Reel	LY62L51216GL-70SLIT	LY62L51216GL-70LLIT



Lyontek Inc.

LY62L51216

Rev. 2.0

512K X 16 BIT LOW POWER CMOS SRAM

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